

BUK7506-55A

N-channel TrenchMOS standard level FET

Rev. 03 — 2 February 2011

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- AEC Q101 compliant
- Low conduction losses due to low on-state resistance
- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V and 24 V loads
- Automotive and general purpose power switching

Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	$T_j \ge 25 ^{\circ}\text{C}; T_j \le 175 ^{\circ}\text{C}$		-	-	55	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 3</u>	[1]	-	-	75	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	300	W
Static char	acteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 175 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see } \frac{\text{Figure 13}}{\text{Figure 13}}}$		-	-	13.2	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } \frac{\text{Figure 12}}{\text{see Figure 13}};$		-	5.3	6.3	mΩ



N-channel TrenchMOS standard level FET

Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\begin{split} I_D &= 75 \text{ A}; V_{\text{sup}} \leq 55 \text{ V}; \\ R_{\text{GS}} &= 50 \Omega; V_{\text{GS}} = 10 \text{ V}; \\ T_{j(\text{init})} &= 25 ^{\circ}\text{C}; \text{unclamped} \end{split}$	-	-	1.1	J

^[1] Continuous current is limited by package.

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain	mb	D
3	S	source		
mb	D	mounting base; connected to drain	1 2 3	mbb076 S
			SOT78A (TO-220AB)	

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7506-55A	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78A

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	55	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	55	V
V _{GS}	gate-source voltage			-20	20	V
I _D	drain current	$T_{mb} = 25 ^{\circ}C; V_{GS} = 10 V; \text{see Figure 1};$	[1]	-	154	Α
		see <u>Figure 3</u>	[2]	-	75	Α
		$T_{mb} = 100 ^{\circ}\text{C}; V_{GS} = 10 \text{V}; \text{see} \frac{\text{Figure 1}}{}$	[2]	-	75	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; see Figure 3		-	616	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	300	W
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drai	in diode					
Is	source current	T _{mb} = 25 °C	[1]	-	154	Α
			[2]	-	75	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	616	Α
Avalanche i	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 75 A; $V_{sup} \le$ 55 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped		-	1.1	J

- [1] Current is limited by power dissipation chip rating.
- [2] Continuous current is limited by package.

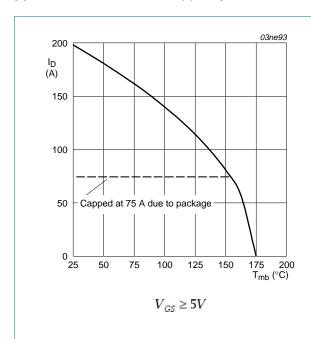


Fig 1. Normalized continuous drain current as a function of mounting base temperature

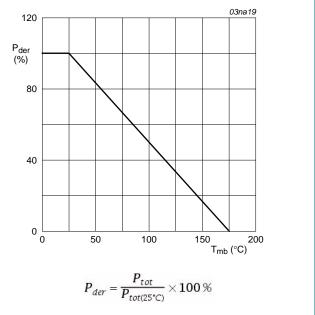
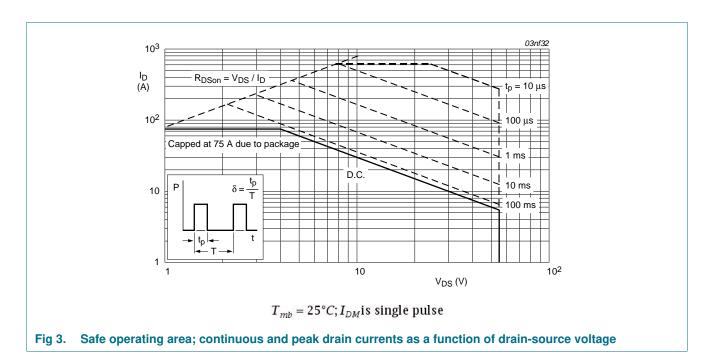


Fig 2. Normalized total power dissipation as a function of mounting base temperature

BUK7506-55A

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5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see Figure 4	-	-	0.5	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W

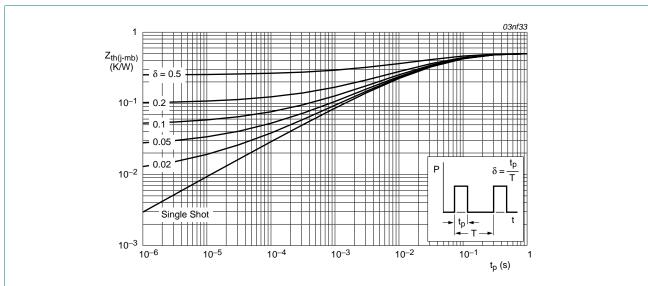


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

6. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					
V _{(BR)DSS}	drain-source	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	55	-	-	V
	breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	50	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 25$ °C; see Figure 11	2	3	4	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = 175$ °C; see Figure 11	1	-	-	V
		$I_D = 1$ mA; $V_{DS} = V_{GS}$; $T_j = -55$ °C; see Figure 11	-	-	4.4	V
I _{DSS} drain leakage current		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μΑ
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.05	10	μΑ
I _{GSS}	gate leakage current	$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
		$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	2	100	nA
DOON	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	-	13.2	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; see <u>Figure 12</u> ; see <u>Figure 13</u>	-	5.3	6.3	mΩ
Dynamic c	haracteristics					
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$	-	4500	6000	рF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 14</u>	-	960	1200	рF
C _{rss}	reverse transfer capacitance		-	510	850	pF
d(on)	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 1.2 \Omega; V_{GS} = 10 \text{ V};$	-	35	-	ns
r	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C$	-	115	-	ns
d(off)	turn-off delay time		-	155	-	ns
f	fall time		-	110	-	ns
L _D	internal drain inductance	from drain lead 6 mm from package to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	4.5	-	nΗ
		from contact screw on mounting base to centre of die ; $T_j = 25 ^{\circ}\text{C}$	-	3.5	-	nΗ
L-s	internal source inductance	from source lead to source bond pad; $T_j = 25 ^{\circ}\text{C}$	-	7.5	-	nΗ
Source-dra	ain diode					
V_{SD}	source-drain voltage	$I_S = 30 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; see <u>Figure 15</u>	-	0.85	1.2	V
rr	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s};$	-	80	-	ns
Q _r	recovered charge $V_{GS} = -10 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 \text{ °C}$		-	200	-	nC

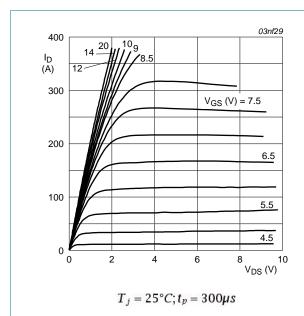


Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values

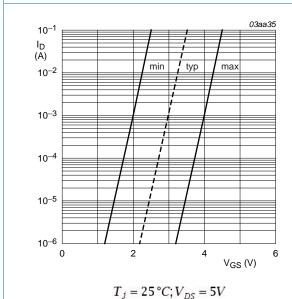


Fig 7. Sub-threshold drain current as a function of gate-source voltage

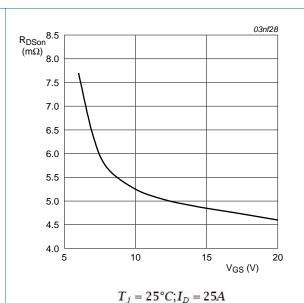


Fig 6. Drain-source on-state resistance as a function of gate-source voltage; typical values

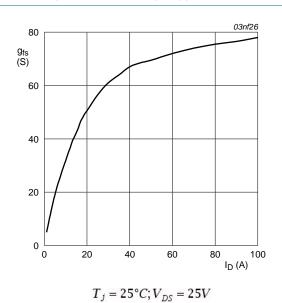


Fig 8. Forward transconductance as a function of drain current; typical values

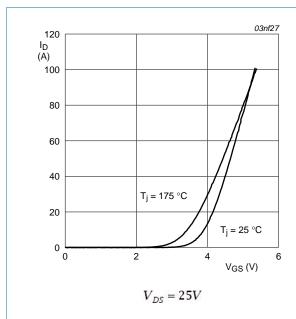


Fig 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

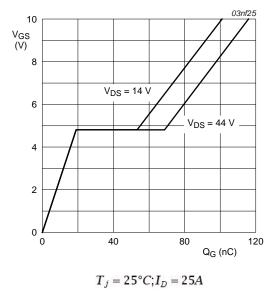


Fig 10. Gate-source voltage as a function of turn-on

gate charge; typical values

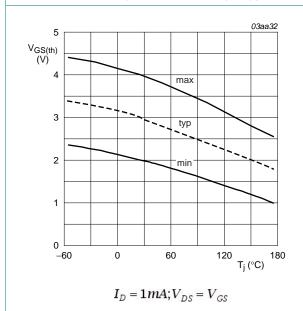


Fig 11. Gate-source threshold voltage as a function of junction temperature

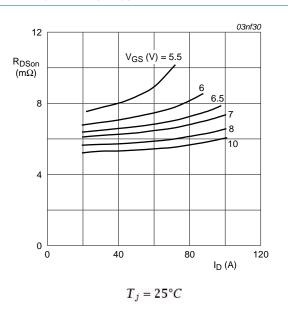
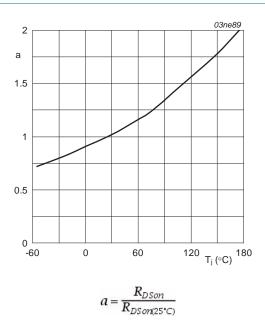


Fig 12. Drain-source on-state resistance as a function of drain current; typical values

N-channel TrenchMOS standard level FET



 $C_{(pF)} = 0000$ $C_{(pF)} = 0000$ $C_{(iss)} = 0000$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

Fig 14. Input and reverse transfer capacitances as a function of drain-source voltage; typical values

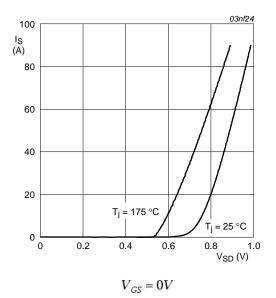


Fig 15. Reverse diode current as a function of reverse diode voltage; typical values

Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78A

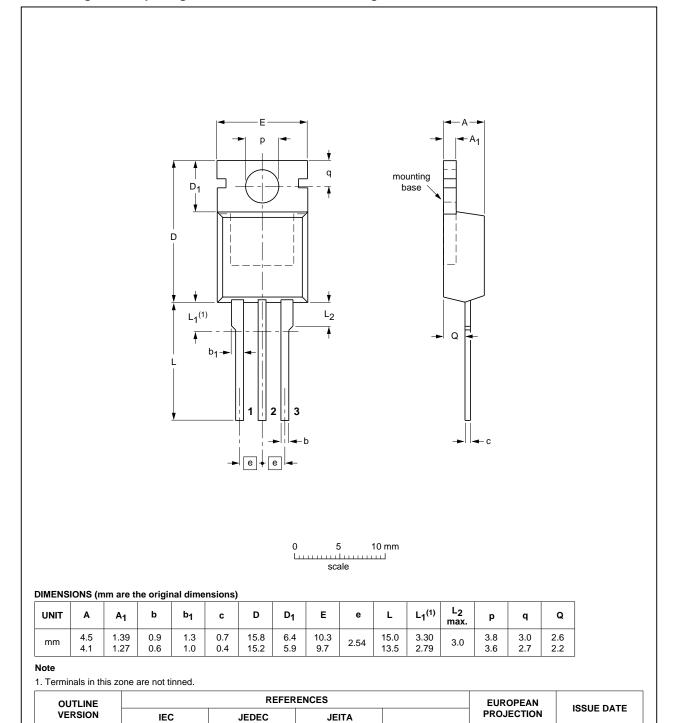


Fig 16. Package outline SOT78A (TO-220AB)

IEC

3-lead TO-220AB

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SOT78A

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8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7506-55A v.3	20110202	Product data sheet	-	BUK7506_7606_55A v.2
Modifications:	 The format of this of NXP Semicono 		esigned to comply w	ith the new identity guidelines
	 Legal texts have 	been adapted to the new	company name who	ere appropriate.
	 Type number BU 	K7506-55A separated fro	m data sheet BUK7	506_7606_55A v.2.
BUK7506_7606_55A v.2	20010703	Product specification	-	-

9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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N-channel TrenchMOS standard level FET

11. Contents

1	Product profile
1.1	General description
1.2	Features and benefits
1.3	Applications
1.4	Quick reference data1
2	Pinning information2
3	Ordering information
4	Limiting values
5	Thermal characteristics4
6	Characteristics
7	Package outline
8	Revision history10
9	Legal information11
9.1	Data sheet status
9.2	Definitions11
9.3	Disclaimers
9.4	Trademarks12
10	Contact information